

FS5AS-06

High-Speed Switching Use Nch Power MOS FET

REJ03G1404-0200

(Previous: MEJ02G0087-0101)

Rev.2.00 Aug 07, 2006

Features

• Drive voltage: 10 V

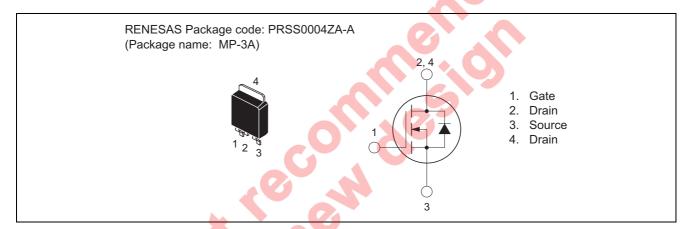
• V_{DSS}: 60 V

• $r_{\rm DS(ON) \, (max)}$: 0.16 Ω

• I_D: 5 A

• Integrated Fast Recovery Diode (TYP.): 45 ns

Outline



Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

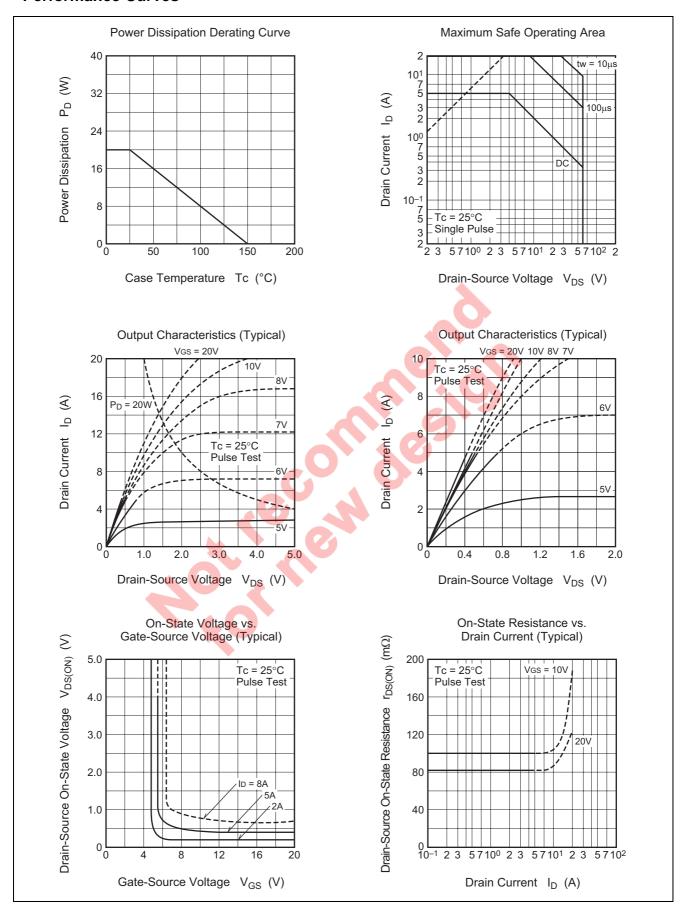
Parameter	Symbol	Ratings	Unit	Conditions	
Drain-source voltage	V _{DSS}	60	V	V _{GS} = 0 V	
Gate-source voltage	V _{GSS}	±20	V	$V_{DS} = 0 V$	
Drain current	I _D	5	Α		
Drain current (Pulsed)	I _{DM}	20	Α		
Avalanche drain current (Pulsed)	I _{DA}	5	Α	L = 100 μH	
Source current	Is	5	Α		
Source current (Pulsed)	I _{SM}	20	Α		
Maximum power dissipation	P _D	20	W		
Channel temperature	Tch	- 55 to +150	°C		
Storage temperature	Tstg	- 55 to +150	°C		
Mass	_	0.32	g	Typical value	

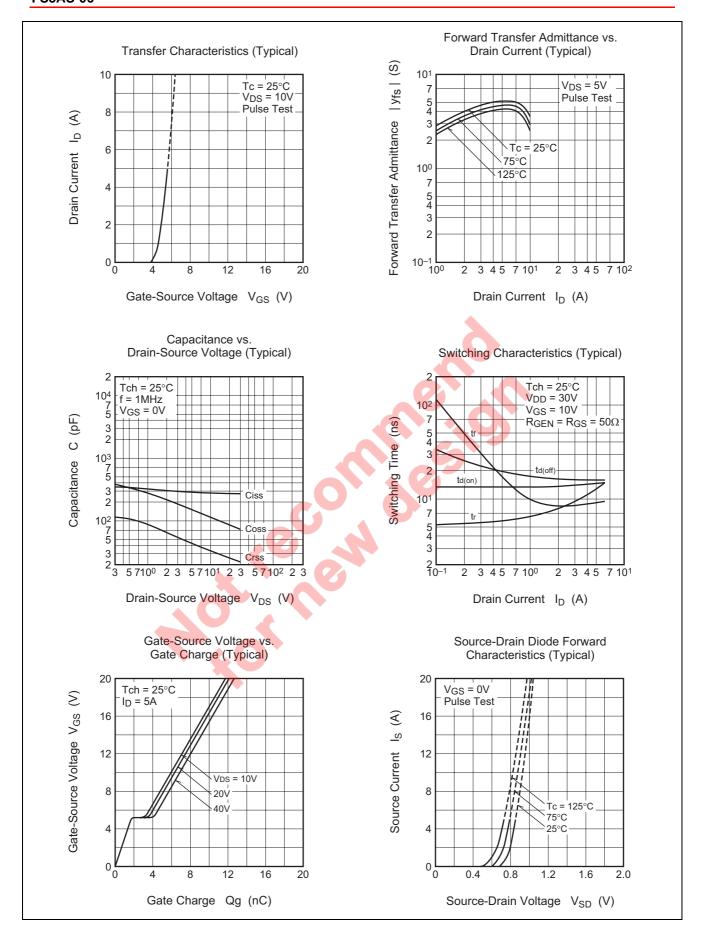
Electrical Characteristics

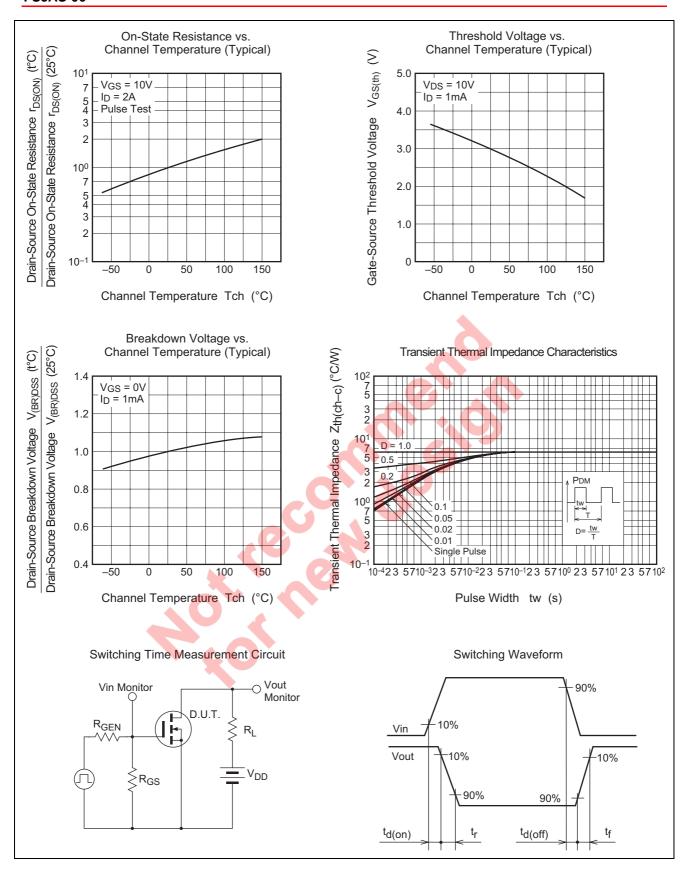
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain-source breakdown voltage	V _{(BR)DSS}	60		_	V	I _D = 1 mA, V _{GS} = 0 V	
Gate-source leakage current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	
Drain-source leakage current	I _{DSS}	_	_	0.1	mA	V _{DS} = 60 V, V _{GS} = 0 V	
Gate-source threshold voltage	V _{GS(th)}	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Drain-source on-state resistance	r _{DS(ON)}	_	0.12	0.16	Ω	I _D = 2 A, V _{GS} = 10 V	
Drain-source on-state voltage	V _{DS(ON)}	_	0.24	0.32	V	I _D = 2 A, V _{GS} = 10 V	
Forward transfer admittance	yfs	_	4.0	_	S	$I_D = 2 A, V_{DS} = 5 V$	
Input capacitance	Ciss	_	280	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output capacitance	Coss	_	120	_	pF	f = 1MHz	
Reverse transfer capacitance	Crss	_	35	_	pF		
Turn-on delay time	t _{d(on)}	_	15	_	ns	$V_{DD} = 30 \text{ V}, I_D = 2 \text{ A},$	
Rise time	t _r	_	8	_	ns	$V_{GS} = 10 \text{ V},$	
Turn-off delay time	t _{d(off)}	_	18	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$	
Fall time	t _f	_	9		ns		
Source-drain voltage	V _{SD}	_	1.0	1.5	V	I _S = 2 A, V _{GS} = 0 V	
Thermal resistance	R _{th(ch-c)}	_	_	6.25	°C/W	Channel to case	
Reverse recovery time	t _{rr}	_	45		ns	$I_S = 5 \text{ A}, d_{is}/d_t = -100 \text{ A/}\mu\text{s}$	
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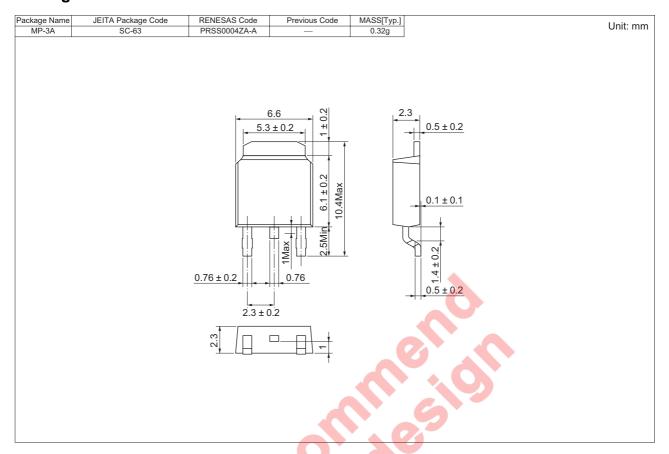
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Qua	antity	Standard order code	Standard order code example
Surface-mounted type	Taping		3000	Type name – T +Direction (1 or 2) +3	FS5AS-06-T13
Surface-mounted type	Plastic Magazine (Tube)		75	Type name	FS5AS-06

Note: Please confirm the specification about the shipping in detail.

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